ABSTRACT OF THE DISCLOSURE

A drive circuit for a semiconductor device comprises an insulated gate transistor (1), a driver (2) for generating a gate voltage having a plurality of voltage levels and applying the generated gate voltage to the transistor (1), and a timing controller (3) for controlling timing of application of the gate voltage with difference voltage levels on the basis of a signal voltage. The driver (2) generates a gate voltage (Va) lower than a threshold voltage of the transistor (1), and a gate voltage (+15 V) as a specified voltage for driving the transistor (1). The timing controller (3) so controls the driver (2) that application of the gate voltage (Va) precedes application of the specified voltage (+15V).